



#### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
30V	1.5Ω @ V <sub>GS</sub> = 4.5V	0.40A
	2.0Ω @ V <sub>GS</sub> = 2.5V	0.35A
	3.0Ω @ V <sub>GS</sub> = 1.8V	0.28A
	4.5Ω @ V <sub>GS</sub> = 1.5V	0.23A

## **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

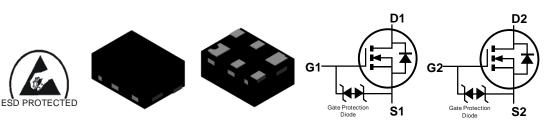
- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

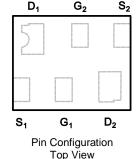
### **Features and Benefits**

- Low On-Resistance
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Ultra-Small Surface Mount Package 0.8mm x 0.6mm
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

### **Mechanical Data**

- Case: X2-DFN0806-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208
- Weight: 0.001 grams (Approximate)





Top View

**Bottom View** 

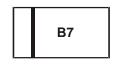
Device Symbol

# Ordering Information (Note 4)

Part Number	Case	Packaging	
DMN31D5UDA-7B	X2-DFN0806-6	10,000/Tape & Reel	

- Notes:
- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

## **Marking Information**



Top View

B7 = Product Type Marking Code

March 2019



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Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			$V_{GSS}$	±12	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	0.4 0.32	А
Maximum Continuous Body Diode Forward Current (Note 6)			Is	0.8	Α
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	0.8	Α

### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

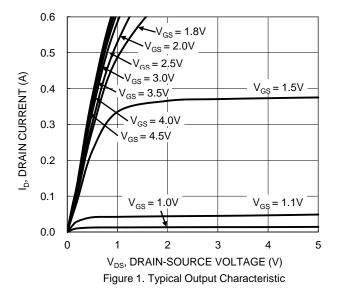
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	$P_{D}$	0.37	W	
Thermal Resistance, Junction to Ambient (Note 5)  Steady State		$R_{\theta JA}$	339	°C/W
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C

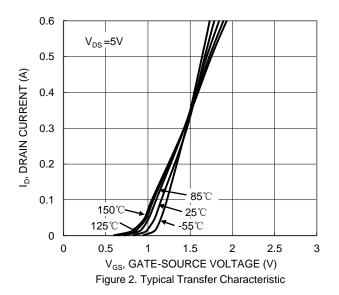
### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

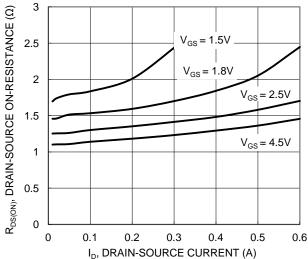
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current @T <sub>C</sub> = +2	5°C I <sub>DSS</sub>	_	_	100	nA	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±10	μA	$V_{GS} = \pm 10V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.4	0.7	1.0	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
		_	1.2	1.5	Ω	$V_{GS} = 4.5V, I_D = 100mA$	
Static Drain-Source On-Resistance	D	_	1.3	2.0		$V_{GS} = 2.5V, I_D = 50mA$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	1.5	3.0		$V_{GS} = 1.8V, I_D = 20mA$	
		_	1.8	4.5		$V_{GS} = 1.5V, I_D = 10mA$	
Diode Forward Voltage		_	0.6	1.0	V	$V_{GS} = 0V$ , $I_S = 10mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	_	22.6	_	pF	V 45V V 6V	
Output Capacitance	Coss	_	2.68	_	pF	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	1.8	_	pF	-1 = 1.0IVIDZ	
Total Gate Charge	Qg	_	0.38	_	nC	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
Gate-Source Charge	Qgs	_	0.05	_	nC	$V_{GS} = 4.5V, V_{DS} = 15V,$ $I_{D} = 200 \text{mA}$	
Gate-Drain Charge	Q <sub>gd</sub>	_	0.07	_	nC		
Turn-On Delay Time	t <sub>D(ON)</sub>	_	3.2	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	2.2	_	ns	$V_{DD} = 15V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	21	_	ns	$R_G = 2\Omega$ , $I_D = 200mA$	
Turn-Off Fall Time	t <sub>F</sub>	_	7.5		ns		

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 6. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
- 7. Short duration pulse test used to minimize self-heating effect.
  8. Guaranteed by design. Not subject to product testing.









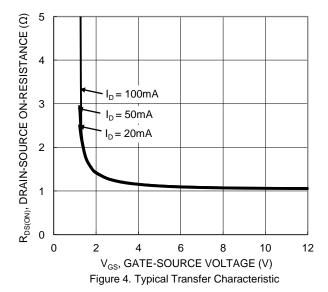
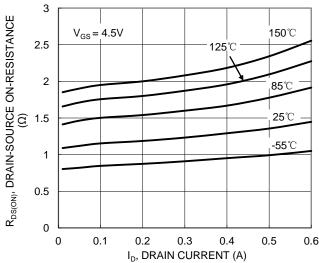


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage



1.8 R<sub>DS(ON)</sub>, DRAIN-SOURCE ON-RESISTANCE 1.6  $V_{GS} = 2.5V, I_D = 50mA$ 1.4 (NORMALIZED)  $V_{GS} = 1.5V, I_{D} = 10mA$ 1.2  $V_{GS} = 1.8V, I_D = 20mA$ 1 8.0 0.6 -25 0 25 100 125 150 -50 50 75 T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

Figure 5. Typical On-Resistance vs. Drain Current and Temperature

Figure 6. On-Resistance Variation with Temperature



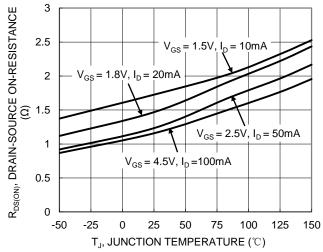


Figure 7. On-Resistance Variation with Temperature

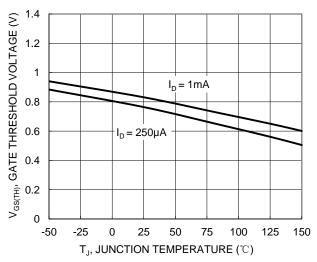
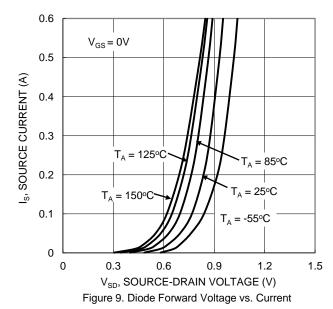


Figure 8. Gate Threshold Variation vs. Junction Temperature



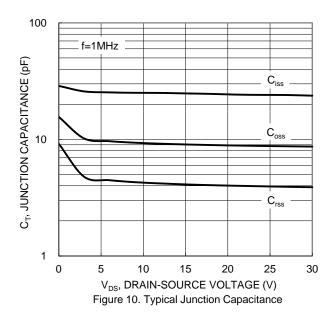
3.5
3  $\geqslant$  2.5  $\Rightarrow$  2
1.5
1
0.5
0

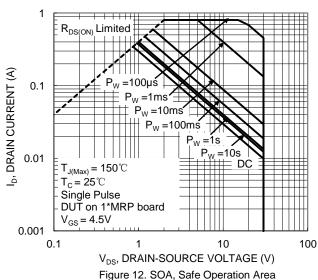
0.2

 ${\bf Q_g}\,({\bf nC})$  Figure 11. Gate Charge

0.3

0.4





0

0.1

4.5

4

0.5



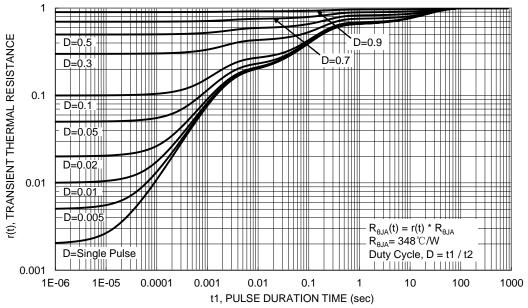


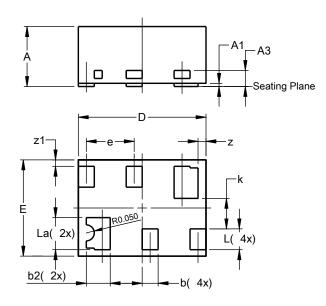
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### X2-DFN0806-6

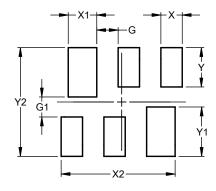


X2-DFN0806-6					
Dim	Min	Max	Тур		
Α		0.40	0.36		
A1	0.00	0.03	0.02		
A3			0.10		
b	0.07	0.15	0.10		
b2	0.10	0.20	0.15		
D	0.75	0.85	0.80		
Е	0.55	0.65	0.60		
е			0.30		
k			0.19		
L	0.10	0.18	0.13		
La	0.17	0.25	0.20		
Z			0.05		
<b>z</b> 1			0.04		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### X2-DFN0806-6



Dimensions	Value (in mm)			
G	0.150			
G1	0.140			
Х	0.150			
X1	0.200			
X2	0.800			
Y	0.275			
Y1	0.345			
Y2	0.760			



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